IN THE CLAIMS:

Listing of claims:

1. (currently amended) A method for forming a head suspension assembly, comprising:

forming a trench extending into a substrate;

forming a sacrificial layer in or on a portion of a substrate the trench;

forming a transfer film across the substrate;

patterning a photoresist layer on top of the transfer film;

transferring the an image of the patterned photoresist layer through the transfer film;

removing the patterned photoresist layer; and

removing the sacrificial layer <u>from the trench</u> to form a cavity extending a distance into the substrate.

- 2. (currently amended) A method as in claim 1, wherein the transfer film includes silicon.
- 3. (currently amended) A method as in claim 1, wherein the transferring the image of the patterned photoresist layer through the transfer film is done using reactive ion etching.
- 4. (original) A method as in claim 1, wherein the substrate comprises silicon and the sacrificial layer is formed by etching a trench in the substrate and filling the trench with a metal.
- 5. (original) A method as in claim 4, wherein removing the sacrificial layer comprises etching the metal from the trench.
- 6. (currently amended) A method as in claim 1, further comprising forming the transfer film from a polymer material.

- 7. (currently amended) A method as in claim 1, wherein the substrate comprises silicon and the transfer film comprises polysilsesquioxone.
- 8. (currently amended) A method as in claim 1, wherein the cavity extends a width that is no greater than that of the <u>substrate</u> suspension arm and the cavity extends a depth that is less than the <u>a</u> depth of the <u>substrate</u>. suspension arm.
- 9. (currently amended) A method as in claim 1, further comprising forming an adhesion layer between the substrate and the transfer film.
- 10. (currently amended) A method as in claim 3, wherein the transfer film comprises a resin, and positioning a slider on the resin after the removing the sacrificial layer.
- 11. (currently amended) A method for forming a head suspension assembly, comprising:

forming a polysilsesquioxone layer over a portion of a substrate; forming a photoresist layer on the polysilsesquioxone layer; patterning the photoresist layer; and etching the polysilsesquioxone layer using the patterned photoresist layer as a mask; and removing the patterned photoresist layer.

- 12. (original) A method as in claim 11, further comprising, prior to forming the photoresist layer, curing the polysilsesquioxone layer.
- 13. (original) A method as in claim 12, further comprising, prior to forming the polysilsesquioxone layer, forming a trench in the substrate and forming a sacrificial layer in the trench, wherein the polysilsesquioxone layer is formed over the sacrificial layer.
- 14. (original) A method as in claim 13, further comprising forming the sacrificial layer from a metal material.

- 15. (original) A method as in claim 13, further comprising forming the sacrificial layer from copper.
- 16. (original) A method as in claim 13, further comprising removing the sacrificial material from the trench after the etching the polysilsesquioxone layer.
- 17. (original) A method as in claim 12, further comprising positioning a slider on the cured polysilsesquioxone layer after the removing the patterned photoresist layer.
 - 18. (new) A method for forming a head suspension assembly, comprising: forming a sacrificial material on a substrate;

forming a layer on the substrate, wherein the sacrificial layer is positioned between a portion of the substrate and a portion of the film;

forming a patterned photoresist on the layer;

etching the layer using the patterned photoresist as a mask;

removing the patterned photoresist after the etching;

removing the sacrificial material after the removing the patterned photoresist layer; and positioning a slider on the etched layer.

- 19. (new) A method as in claim 18, wherein the layer comprises a polysilsesquioxone material.
- 20. (new) A method as in claim 18, further comprising forming a trench in the substrate and forming the sacrificial material in the trench.